

UNIVERSITY OF MYSORE

Ph.D. Entrance Examination, November - 2020

SUBJECT CODE : 23

Entrance Reg. No.

QUESTION BOOKLET NO.

503146

QUESTION BOOKLET

(Read carefully the instructions given in the Question Booklet)

SUBJECT:

ELECTRONICS

MAXIMUM MARKS: 100

MAXIMUM TIME: THREE HOURS

(Including initial 10 minutes for filling O.M.R. Answer sheet)

INSTRUCTIONS TO THE CANDIDATES

- 1. The sealed questions booklet containing 50 questions enclosed with O.M.R. Answer Sheet is given to you.
- 2. Verify whether the given question booklet is of the same subject which you have opted for examination.
- 3. Open the question paper seal carefully and take out the enclosed O.M.R. Answer Sheet outside the question booklet and fill up the general information in the O.M.R. Answer sheet. If you fail to fill up the details in the form of alphabet and signs as instructed, you will be personally responsible for consequences arising during scoring of your Answer Sheet.
- 4. During the examination:
 - a) Read each question carefully.
 - b) Determine the Most appropriate/correct answer from the four available choices given under each question.
 - c) Completely darken the relevant circle against the Question in the O.M.R. Answer Sheet. For example, in the question paper if "C" is correct answer for Question No.8, then darken against Sl. No.8 of O.M.R. Answer Sheet using Blue/Black Ball Point Pen as follows:

Question No. 8. (A) (B) (Only example) (Use Ball Pen only)

- 5. Rough work should be done only on the blank space provided in the Question Booklet. Rough work should not be done on the O.M.R. Answer Sheet.
- 6. <u>If more than one circle is darkened for a given question, such answer is treated as wrong and no mark will be given. See the example in the O.M.R. Sheet.</u>
- 7. The candidate and the Room Supervisor should sign in the O.M.R. Sheet at the specified place.
- 8. Candidate should return the original O.M.R. Answer Sheet and the university copy to the Room Supervisor after the examination.
- 9. Candidate can carry the question booklet and the candidate copy of the O.M.R. Sheet.
- 10. The calculator, pager and mobile phone are not allowed inside the examination hall.
- 11. If a candidate is found committing malpractice, such a candidate shall not be considered for admission to the course and action against such candidate will be taken as per rules.

INSTRUCTIONS TO FILL UP THE O.M.R. SHEET

- 1. There is only one most appropriate/correct answer for each question.
- 2. For each question, only one circle must be darkened with BLUE or BLACK ball point pen only. Do not try to alter it.
- 3. Circle should be darkened completely so that the alphabet inside it is not visible.
- 4. Do not make any stray marks on O.M.R. Sheet.

ಗಮನಿಸಿ : ಸೂಚನೆಗಳ ಕನ್ನಡ ಆವೃತ್ತಿಯು ಈ ಮಸ್ತಕದ ಹಿಂಭಾಗದಲ್ಲಿ ಮುದ್ರಿಸಲ್ಪಟ್ಟಿದೆ.



		PAR	<u>T - A</u>					
Th	is pa	rt shall contains 50 multiple	choice/o	bjective type questions, eac				
que	estion	carrying one mark.		[50×1=50				
1)	AP	-N junction mimics a closed sw	itch wher	n it				
	(A)	Cannot overcome its barrier vo	oltage	the second section of				
	(B)	Has a low junction resistance						
	(C)	Is reverse biased						
	(D)	Has a wide depletion region						
2)		en a common-collector will be etion(s) of this stage is to:	the last	stage before the load; the mai				
	(A)	Provide voltage gain						
	(B)	Provide phase inversion		The state of the s				
	(C)	Provide a high-frequency path	to impro	ve the frequency response				
	(D)	Buffer the voltage amplifiers in impedance matching for maxin						
3)	The	The JFET is also known as square law device because its						
	(A)	A) Drain current varies as square of the gate source voltage						
	(B)	Transconductance curve is par	abolic	s and take to be a consoling that the				
	(C)	Reverse gate leakage current v	aries as s	quare of reverse gate voltage				
	(D)	Drain current varies as square	of its drai	n voltage for a fixed Vgs				
4)	Which of the following diode exhibits negative resistance region							
	(A)	PN-junction diode	(B)	Zener diode				
	(C)	Schottky diode	(D)	Tunnel diode				
5)	An amplifier has a voltage gain of 100 V/V and a current gain of 1000A/A. value of the power gain decibel is							
	(A)	30db	(B)	40db				
	(C)	50db	(D)	100db				
6)	Whi	ich logic is the fastest of all the lo	ogic fami	lies?				
	(A)	TTL	(B)	ECL				
	(0)	TPP	(D)	DIT				

7)	A ring counter consisting of 4 flip-flops will have				
	(A)	4 States	(B)	8 States	
	(C)	16 States	(D)	Infinite states	
0)	_				
8)	Determine the output frequency for a frequency division circuit that contain 12 flip-flops with an input clock frequency of 20.48 MHz.				
		1.7067 MkHz		5 kHz	
	(C)	30.24 kHz	(D)	15 kHz	
9)	digit	tal-to-analog converter is an applicat	ion o	fthe	
"	1		JOHO	Le sgrigger great Killer	
	(A)	Voltage-to-current converter			
	(B)	Scaling adder			
	(C)	Noninverting amplifier		A the Market of the Carlo	
	(D)	Current-to-voltage converter			
10)	0) Sample-and-hold circuits in ADCs are designed to				
10,	e de la composition				
	(A)	Sample and hold the output of the laprocess	binar	y counter during the conversion	
	(B)	Stabilize the ADCs threshold volta	ge du	ring the conversion process	
	(C)	Stabilize the input analog signal du	ring	the conversion process	
	(D)	Sample and hold the ADC stairca process		aveform during the conversion	
11)	Mes	sh analysis is generally used to deter	mine	State and the second section of the section of	
	(A)	Voltage	(B)	Current	
	(C)	Resistance	(D)	Power	

	(C)	10.6V	(D)	15V			
		den habitoriari mpyoresi - i					
13)	The	correct relation between energy	y and char	ge is			
	(A)	Energy = voltage / charge					
	(B)	Charge = Energy × voltage		5.4.2956.17F SW.75.1			
	(C)	Energy = voltage \times (charge) \times	0.5				
	(D)	Energy = voltage \times charge					
14)		sider the equation $s^3 + 3s^2 + 5s^2$ half of s-plane?	s+2=0.	How many roots are located			
	(A)	Zero	(B)	· Two			
	(C)	Three	(D)	Four			
15)	Which one of the following is not the property of root loci?						
	(A) The root locus is symmetrical about imaginary axis						
	(B) They start from the open loop poles and terminate at the open loop zeroes						
	(C)	The breakaway points are dete	ermined fi	rom dK/ds = 0			
	(D)	Segments of the real axis are total number of real poles and					
16)	The	number of software interrupts	in 8085 is	ring to the state of the state			
	(A)	5	(B)	8			
	(C)	9	(D)	10			
M	5250		4-				

12) The rms value of the voltage for a voltage function $v=10+5\cos(628t+300)v$

(B) 10V

through a circuit is

(A) 5V

17)	Arrange the following instructions of 8085 in descending order w.r.t number of machine cycle				
	i)	LHLD			
	ii)	ADD M			
	iii)	JNC			
	iv)	STA		The state of the s	
	(A)	i, iv, iii, ii	(B)	iv, i, ii, iii	
	(C)	i, iv, ii, iii	(D)	ii, iii,iv,i	
18)		register which holds the information logic operations is called as	about	the nature of results of arithmetic	
	(A)	Accumulator			
	(B)	Condition code register			
	(C)	Flag register			
	(D)	Process status register			
	,				
19)	For	DIV BX instruction of 8086 the div	idend	must be in	
	(A)	AX	(B)	BX	
	(C)	DXAX	(D)	BXAX	
20)	Whi	ch of the following register can be	addre	ssed as byte?	
	(A)	P1 (3)	(B)	SCON	
	(C)	TMOD	(D)	TCON	
21)	A 40 is	00W carrier is amplitude modulated	with i	m = 0.75. The total power in AM	
	(A)	400W	(B)	512W	
	(C)	588W	(D)	650W	

M-5250

P.T.O.

(A) $C = log_2N$ (B) $C = (\delta f)log_2N$ (C) $C = 2(\delta f)log_2N$ (D) $C = 0.5(\delta f)log_2N$ 23) Signal to quantization noise ratio in PCM system depends on	22)	In the absence of noise, if C is channel capacity in bits/s, δf is channel bandwidth in Hz and N is number of coding levels. Then				
23) Signal to quantization noise ratio in PCM system depends on		(A)	$C = \log_2 N$	(B)	$C = (\delta f) \log_2 N$	
(A) Sampling rate (B) Signal bandwidth (C) Number of quantization levels (D) Nature of carrier wave 24) If the baud rate is 400 for a QPSK, the bit rate is bps. (A) 400 (B) 800 (C) 1200 (D) 1600 25) The band gap energy of germanium at 300k is (A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°		(C)	$C = 2(\delta f) \log_2 N$	(D)	$C = 0.5(\delta f)\log_2 N$	
(C) Number of quantization levels (D) Nature of carrier wave 24) If the baud rate is 400 for a QPSK, the bit rate is bps. (A) 400 (B) 800 (C) 1200 (D) 1600 25) The band gap energy of germanium at 300k is (A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°	23)	Sign	nal to quantization noise ratio in PC	M sy	stem depends on	
24) If the baud rate is 400 for a QPSK, the bit rate is bps. (A) 400 (B) 800 (C) 1200 (D) 1600 25) The band gap energy of germanium at 300k is (A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°		(A)	Sampling rate	(B)	Signal bandwidth	
(A) 400 (B) 800 (C) 1200 (D) 1600 25) The band gap energy of germanium at 300k is (A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°		(C)	Number of quantization levels	(D)	Nature of carrier wave	
(A) 400 (B) 800 (C) 1200 (D) 1600 25) The band gap energy of germanium at 300k is (A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°						
(C) 1200 (D) 1600 25) The band gap energy of germanium at 300k is (A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°	24)	If th	e baud rate is 400 for a QPSK, the	bit ra	te is bps.	
25) The band gap energy of germanium at 300k is (A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°		(A)	400	(B)	800	
(A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°		(C)	1200	(D)	1600	
(A) 0.785 ev (B) 1.121 ev (C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°						
(C) 1.212 ev (D) 0.718 ev 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°	25)	The band gap energy of germanium at 300k is				
 26) If the current of an SCR increases, the forward breakdown voltage will (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90° 		(A)	0.785 ev	(B)	1.121 ev	
 (A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90° 		(C)	1.212 ev	(D)	0.718 ev	
(A) Decreases (B) Not be effected (C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°						
(C) Increases (D) Becomes zero 27) The maximum delay angle that can be achieved with an R-trigger circuit is (A) 45° (B) 90°	26)	If th	e current of an SCR increases, the fo	orwar	d breakdown voltage will	
27) The maximum delay angle that can be achieved with an R-trigger circuit is(A) 45°(B) 90°		(A)	Decreases	(B)	Not be effected	
(A) 45° (B) 90°		(C)	Increases	(D)	Becomes zero	
(A) 45° (B) 90°						
	27) The maximum delay angle that can be achieved with an R-trigger circuit is					
(C) 180° (D) 120°		(A)	45°	(B)	90°	
		(C)	180°	(D)	120°	

2	8)	(A)	function of a snubber circuit connected across an SCR is to Suppress dv/dt Increase dv/dt
		` '	Decrease dv/dt
		(D)	Keep transient voltage at a constant value
2	9)	The	commutation circuit used in the controlled rectifiers is to
		(A)	Turn-on the thyristors
		(B)	Turn-off the thyristors
		(C)	To increase the frequency of operation of the controlled rectifiers
		(D)	To convert ac signal into dc signal
3	0)		main reason for the connecting of a pulse transformer at the output see thyristor triggering circuit is to
		(A)	Amplify the power of the triggering pulse.
			16:20 MB - CONTROL OF

- (B) Provide electrical isolation.
- (C) Reduce the turn on time of thyristor.
- (D) Avoid spurious triggering of the thyristor due to noise.
- 31) Do-While loop is example for
 - (A) Exit checking loop

(B) Entry checking loop

(C) No checking loop

- (D) Middle checking loop
- 32) For initialization a = 5, c = 6 the value of a and c after this code will be c = (c) ? a = 0 : 2;
 - (A) a = 0, c = 0;

(B) a = 0, c = 6;

(C) a = 5, c = 6;

- (D) a = 0, c = 2;
- 33) Maximum value of an unsigned integer is
 - (A) 65535

(B) 32767

(C) 255

(D) 127

34) What will happen if the following C code is executed main()

int x[5]; x[5]=10;

}

(A) It will not be allowed, but no error message will be generated

(B) Compiler will generate an error message

(C) Fifth element of an array x will be assigned with value 10

(D) Some other data may be overwritten

35) What is size of generic pointer in c?

(A) Obytes

(B) 1bytes

(C) 2bytes

(D) 3bytes

36) Discrete-time sinusoids whose frequencies are separated by an integer multiples of _____ are identical.

(A) $\frac{\pi}{2}$

(B) π

(C) $\frac{3\pi}{2}$

(D) 2π

37) The output of a causal system depends on

- (A) Present and future inputs
- (B) Present and past inputs
- (C) Present input and present output
- (D) Past inputs and present output

38) In x(n) is the input to the system having the impulse response h(n), then the expression for the convolution sum y(n) is

(A)
$$y(n) = \sum_{k=-\infty}^{\infty} x(k)h(n-k)$$

(B)
$$y(n) = \sum_{k=-\infty}^{\infty} x(n)h(n-k)$$

(C)
$$y(n) = \sum_{k=0}^{N-1} x(k)h(n-k)$$

(D)
$$y(n) = \sum_{k=0}^{N-1} x(n)h(n-k)$$

39)	In MOSFET devices, the N-Channel type is better than the P-Channel type in the following respect.							
	(A)	It has better noise immunity	(B)	It is faster				
	(C)	It is TTL compatible	(D)	It has better drive capability				
40)	The	The real-valued continuous-time periodic signal has						
	(A)	(A) Line spectrum and its magnitude spectrum is even function						
	(B)	B) Line spectrum and its phase spectrum is even function						
	(C)	(C) Continuous spectrum and its magnitude spectrum is even function						
	(D)	Continuous spectrum and its phase	e spec	etrum is even				
41)	The	function of SiO ₂ layer in IC fabrica	tion is	s vicking succession assets.				
	(A)	Oxide masking	(B)	Oxide passivation				
	(C)	Oxide purification	(D)	Both (A) & (B)				
42)	Epitaxial growth is best suited for							
	(A)	(A) Growing polycrystalline pure silicon						
	(B)	(B) Growing crystal of several inch thickness						
	(C)	(C) Very thick single crystal on a substrate						
	(D)	(D) Very thin single crystal on a substrate						
43)	Why MOSFET is preferred over BJT in IC components?							
	(A) MOSFET has low packing density							
	(B)	B) MOSFET has medium packing density						
	(C)							
	(D)	MOSFET has no packing density						
		Arguly (1911) and the conver- sion of the conver-						
44)	Large scale integration chips have between							
	(A)	Less than 10 components	(B)	100 and 1000 components				
	(C)	10 and 100 components	(D)	More than 1000 components				

45)	Wh	ich is the final step in IC processing	sequ	ence
	(A)	Photolithography	(B)	Chemical Vapour
. 7	(C)	Metallization	(D)	Oxidation
46)	In a	n optical fiber, the concept of Numer ability of	ical a _l	perture is applicable in describing
	(A)	Light Collection	(B)	Light Scattering
	(C)	Light Dispersion	(D)	Light Polarization
47)		pontaneous emission, the light sou sition to a state with	rce in	an excited state undergoes the
	(A)	Higher energy	(B)	Moderate energy
	(C)	Lower energy	(D)	Zero Energy
48)			erical	aperture aperture
49)	mov (A)	ch among the following characterist rement of all individual light waves t Monochromatic Coherent	ics of ogeth (B)	Laser light specifies the precise
50)	reger (A)	ch among the following is proving a proving the following is proving the second proving t	ded l	by an optical receiver for the
				emorato del mas de 12 - 25

PART - B

This part shall contains five questions, each question carrying ten marks. $[5 \times 10 = 50]$

- Design full subtractor and show the implementation of full subtractor using basic gates and only NAND gates.
- 2. With neat block diagram briefly explain internal architecture of 8086 microprocessor.
- 3. Explain if-else and switch statements with suitable example program.
- 4. Write a note on ASK, FSK, PSK, DPSK and QPSK
- 5. Explain various types of signals.



ಅಭ್ಯರ್ಥಿಗಳಿಗೆ ಸೂಚನೆಗಳು

- 1. ಓ.ಎಂ.ಆರ್. ಉತ್ತರ ಹಾಳೆಯ ಜೊತೆಗೆ 50 ಪ್ರಶ್ನೆಗಳನ್ನು ಹೊಂದಿರುವ ಮೊಹರು ಮಾಡಿದ ಪ್ರಶ್ನೆ ಮಸ್ತಕವನ್ನು ನಿಮಗೆ ನೀಡಲಾಗಿದೆ.
- 2. ಕೊಟ್ಟಿರುವ ಪ್ರಶ್ನೆ ಮಸ್ತಕವು, ನೀವು ಪರೀಕ್ಷೆಗೆ ಆಯ್ಕೆ ಮಾಡಿಕೊಂಡಿರುವ ವಿಷಯಕ್ಕೆ ಸಂಬಂಧಿಸಿದ್ದೇ ಎಂಬುದನ್ನು ಪರಿಶೀಲಿಸಿರಿ.
- 3. ಪ್ರಶ್ನೆ ಪತ್ರಿಕೆಯ ಮೊಹರನ್ನು ಜಾಗ್ರತೆಯಿಂದ ತೆರೆಯಿರಿ ಮತ್ತು ಪ್ರಶ್ನೆಪತ್ರಿಕೆಯಿಂದ ಓ.ಎಂ.ಆರ್. ಉತ್ತರ ಹಾಳೆಯನ್ನು ಹೊರಗೆ ತೆಗೆದು, ಓ.ಎಂ.ಆರ್. ಉತ್ತರ ಹಾಳೆಯಲ್ಲಿ ಸಾಮಾನ್ಯ ಮಾಹಿತಿಯನ್ನು ತುಂಬಿರಿ. ಕೊಟ್ಟಿರುವ ಸೂಚನೆಯಂತೆ ನೀವು ನಮೂನೆಯಲ್ಲಿನ ವಿವರಗಳನ್ನು ತುಂಬಲು ವಿಫಲರಾದರೆ, ನಿಮ್ಮ ಉತ್ತರ ಹಾಳೆಯ ಮೌಲ್ಯಮಾಪನ ಸಮಯದಲ್ಲಿ ಉಂಟಾಗುವ ಪರಿಣಾಮಗಳಿಗೆ ವೈಯಕ್ತಿಕವಾಗಿ ನೀವೇ ಜವಾಬ್ದಾರರಾಗಿರುತ್ತೀರಿ.
- 4. ಪರೀಕ್ಷೆಯ ಸಮಯದಲ್ಲಿ:
 - a) ಪ್ರತಿಯೊಂದು ಪ್ರಶ್ನೆಯನ್ನು ಜಾಗ್ರತೆಯಿಂದ ಓದಿರಿ.
 - b) ಪ್ರತಿ ಪ್ರಶ್ನೆಯ ಕೆಳಗೆ ನೀಡಿರುವ ನಾಲ್ಕು ಲಭ್ಯ ಆಯ್ಕೆಗಳಲ್ಲಿ ಅತ್ಯಂತ ಸರಿಯಾದ/ ಸೂಕ್ತವಾದ ಉತ್ತರವನ್ನು ನಿರ್ಧರಿಸಿ.
 - c) ಓ.ಎಂ.ಆರ್. ಹಾಳೆಯಲ್ಲಿನ ಸಂಬಂಧಿಸಿದ ಪ್ರಶ್ನೆಯ ವೃತ್ತಾಕಾರವನ್ನು ಸಂಪೂರ್ಣವಾಗಿ ತುಂಬಿರಿ. ಉದಾಹರಣೆಗೆ, ಪ್ರಶ್ನೆ ಪತ್ರಿಕೆಯಲ್ಲಿ ಪ್ರಶ್ನೆ ಸಂಖ್ಯೆ 8ಕ್ಕೆ "C" ಸರಿಯಾದ ಉತ್ತರವಾಗಿದ್ದರೆ, ನೀಲಿ/ಕಪ್ಪು ಬಾಲ್ ಪಾಯಿಂಟ್ ಪೆನ್ ಬಳಸಿ ಓ.ಎಂ.ಆರ್. ಉತ್ತರ ಹಾಳೆಯ ಕ್ರಮ ಸಂಖ್ಯೆ 8ರ ಮುಂದೆ ಈ ಕೆಳಗಿನಂತೆ ತುಂಬಿರಿ:
 - ಪ್ರಶ್ನೆ ಸಂಖ್ಯೆ 8.♠ ฿ Ѻ (ಉದಾಹರಣೆ ಮಾತ್ರ) (ಬಾಲ್ ಪಾಯಿಂಟ್ ಪೆನ್ ಮಾತ್ರ ಉಪಯೋಗಿಸಿ)
- 5. ಉತ್ತರದ ಪೂರ್ವಸಿದ್ದತೆಯ ಬರವಣಿಗೆಯನ್ನು (ಚಿತ್ತು ಕೆಲಸ) ಪ್ರಶ್ನೆ ಪತ್ರಿಕೆಯಲ್ಲಿ ಒದಗಿಸಿದ ಖಾಲಿ ಜಾಗದಲ್ಲಿ ಮಾತ್ರವೇ ಮಾಡಬೇಕು (ಓ.ಎಂ.ಆರ್. ಉತ್ತರ ಹಾಳೆಯಲ್ಲಿ ಮಾಡಬಾರದು).
- 6. ಒಂದು ನಿರ್ದಿಷ್ಟ ಪ್ರಶ್ನೆಗೆ ಒಂದಕ್ಕಿಂತ ಹೆಚ್ಚು ವೃತ್ತಾಕಾರವನ್ನು ಗುರುತಿಸಲಾಗಿದ್ದರೆ, ಅಂತಹ ಉತ್ತರವನ್ನು ತಪ್ಪು ಎಂದು ಪರಿಗಣಿಸಲಾಗುತ್ತದೆ ಮತ್ತು ಯಾವುದೇ ಅಂಕವನ್ನು ನೀಡಲಾಗುವುದಿಲ್ಲ. ಓ.ಎಂ.ಆರ್. ಹಾಳೆಯಲ್ಲಿನ ಉದಾಹರಣೆ ನೋಡಿ.
- 7. ಅಭ್ಯರ್ಥಿ ಮತ್ತು ಕೊಠಡಿ ಮೇಲ್ವಿಚಾರಕರು ನಿರ್ದಿಷ್ಟಪಡಿಸಿದ ಸ್ಥಳದಲ್ಲಿ ಓ.ಎಂ.ಆರ್. ಹಾಳೆಯ ಮೇಲೆ ಸಹಿ ಮಾಡಬೇಕು.
- 8. ಅಭ್ಯರ್ಥಿಯು ಪರೀಕ್ಷೆಯ ನಂತರ ಕೊಠಡಿ ಮೇಲ್ವಿಚಾರಕರಿಗೆ ಮೂಲ ಓ.ಎಂ.ಆರ್. ಉತ್ತರ ಹಾಳೆ ಮತ್ತು ವಿಶ್ವವಿದ್ಯಾನಿಲಯದ ಪ್ರತಿಯನ್ನು ಹಿಂದಿರುಗಿಸಬೇಕು.
- 9. ಅಭ್ಯರ್ಥಿಯ ಪ್ರಶ್ನೆ ಮಸ್ತಕವನ್ನು ಮತ್ತು ಓ.ಎಂ.ಆರ್. ಅಭ್ಯರ್ಥಿಯ ಪ್ರತಿಯನ್ನು ತಮ್ಮ ಜೊತೆ ತೆಗೆದುಕೊಂಡು ಹೋಗಬಹುದು.
- 10. ಕ್ಯಾಲ್ಕುಲೇಟರ್, ಪೇಜರ್ ಮತ್ತು ಮೊಬೈಲ್ ಘೋನ್ ಗಳನ್ನು ಪರೀಕ್ಷಾ ಕೊಠಡಿಯ ಒಳಗೆ ಅನುಮತಿಸಲಾಗುವುದಿಲ್ಲ.
- 11. ಅಭ್ಯರ್ಥಿಯು ದುಷ್ಕ್ರತ್ಯದಲ್ಲಿ ತೊಡಗಿರುವುದು ಕಂಡುಬಂದರೆ, ಅಂತಹ ಅಭ್ಯರ್ಥಿಯನ್ನು ಕೋರ್ಸ್ಗೆ ಪರಿಗಣಿಸಲಾಗುವುದಿಲ್ಲ ಮತ್ತು ನಿಯಮಗಳ ಪ್ರಕಾರ ಇಂತಹ ಅಭ್ಯರ್ಥಿಯ ವಿರುದ್ಧ ಕ್ರಮ ಕೈಗೊಳ್ಳಲಾಗುವುದು. <u>ಓ.ಎಂ.ಆರ್. ಹಾಳೆಯನ್ನು ತುಂಬಲು ಸೂಚನೆಗಳು</u>
- 1. ಪ್ರತಿಯೊಂದು ಪ್ರಶ್ನೆಗೆ ಒಂದೇ ಒಂದು ಅತ್ಯಂತ ಸೂಕ್ತವಾದ/ಸರಿಯಾದ ಉತ್ತರವಿರುತ್ತದೆ.
- 2. ಪ್ರತಿ ಪ್ರಶ್ನೆಗೆ ಒಂದು ವೃತ್ತವನ್ನು ಮಾತ್ರ ನೀಲಿ ಅಥವಾ ಕಪ್ಪು ಬಾಲ್ ಪಾಯಿಂಟ್ ಪೆನ್ನಿನಿಂದ ಮಾತ್ರ ತುಂಬತಕ್ಕದ್ದು, ಉತ್ತರವನ್ನು ಮಾರ್ಪಡಿಸಲು ಪ್ರಯತ್ನಿಸಬೇಡಿ.
- 3. ವೃತ್ತದೊಳಗಿರುವ ಅಕ್ಷರವು ಕಾಣದಿರುವಂತೆ ವೃತ್ತವನ್ನು ಸಂಪೂರ್ಣವಾಗಿ ತುಂಬುವುದು.
- 4. ಓ.ಎಂ.ಆರ್. ಹಾಳೆಯಲ್ಲಿ ಯಾವುದೇ ಅನಾವಶ್ಯಕ ಗುರುತುಗಳನ್ನು ಮಾಡಬೇಡಿ.

Note: English version of the instructions is printed on the front cover of this booklet.

